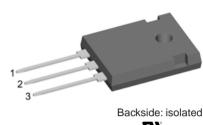
## SiC Schottky Diode

Ultra fast switching Zero reverse recovery **Common Cathode** 

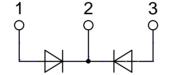
Part number DCG20C1200HR

#### tentative V<sub>RRM</sub> = 1200 V

 $I_{EAV} = 2x \ 12.5 \ A$ 



**E**72873



#### Features / Advantages:

- Ultra fast switching
- · Zero reverse recovery
- · Zero forward recovery
- Temperature independent switching behavior
- · Positive temperature coefficient of forward voltage
- T<sub>VJM</sub> = 175°C

#### **Applications:**

- Solar inverter
- Uninterruptible power supply (UPS)
- Welding equipment
- Switched-mode power supplies
- Medical equipment
- High speed rectifier

#### Package: ISO247

- Isolation Voltage: 3600 V~
- · Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- · Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms & Conditions of Usage The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you. Due to technical requirements our product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend - to perform joint risk and quality assessments;

the conclusion of quality agreements;
to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures

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### DCG20C1200HR

#### tentative

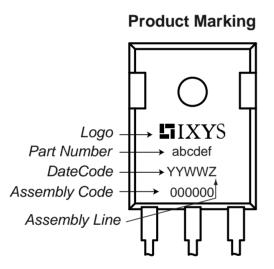
SiC Diod	e (per diode)		Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	
V <sub>RSM</sub>	max. non-repetitive reverse blocking voltage			ĺ	1200	V
V <sub>RRM</sub>	max. repetitive reverse blocking voltage	$T_{vJ} = 25^{\circ}C$			1200	V
I <sub>R</sub>	reverse current	$V_{R} = V_{RRM} \qquad \qquad T_{VJ} = 25^{\circ}C \\ T_{VJ} = 175^{\circ}C$		30 55	250 350	μΑ μΑ
V <sub>F</sub>	forward voltage	$I_F = 10 \text{ A}$ $T_{VJ} = 25^{\circ}\text{C}$ $I_F = 20 \text{ A}$		1.5	1.8	V V
		$I_F = 10 \text{ A}$ $T_{VJ} = 175^{\circ}\text{C}$ $I_F = 20 \text{ A}$		2.2	3.0	V V
I <sub>FAV</sub>	average forward current	$ \begin{array}{ccc} T_{c} = & 80^{\circ}C \\ T_{c} = & 100^{\circ}C \end{array} \end{array} rectangular, d = 0.5 \\ T_{vJ} = & 175^{\circ}C \end{array} $			12.5 11	A A
I <sub>F25</sub> I <sub>F80</sub> I <sub>F100</sub>	forward current	based on typ. $V_{F0}$ and $r_F$ $T_C = 25^{\circ}C$ $T_C = 80^{\circ}C$ $T_C = 100^{\circ}C$			22 17 15	A A A
I <sub>FSM</sub>	max forward surge current	t = 10 ms,half sine (50 Hz) $t_p = 10 \ \mu$ s, pulse $T_{VJ} = 25^{\circ}C$ $V_R = 0V$			750	A A
$V_{\rm F0}$	threshold voltage	T <sub>vJ</sub> = 125°C 175°C		0.77 0.69		V V
r <sub>F</sub>	slope resistance	$\int \text{ for power loss calculation} \\ T_{VJ} = 125^{\circ}C \\ 175^{\circ}C$		107 133		mΩ mΩ
Q <sub>c</sub>	total capacitive charge	$V_{R} = 800 \text{ V}, I_{F} = 10 \text{ A}$ $T_{VJ} = 25^{\circ}\text{C}$ dl/dt = 200 A/µs		52		nC
С	total capacitance	$\left. \begin{array}{c} V_{R} = 0 \ V \\ V_{R} = 400 \ V \\ V_{R} = 800 \ V \end{array} \right\} \hspace{1.5cm} T_{VJ} = 25^{\circ}C, \ f = 1 \ MHz$		755 45 38		pF pF pF
R <sub>thJC</sub> R <sub>thJH</sub>	thermal resistance junction to case thermal resistance junction to heatsink	with heatsink compound; IXYS test setup		2.2	1.9	K/W K/W



### DCG20C1200HR

#### tentative

Package	ISO247			Rating	s	
Symbol	Definitions	Conditions	min.	typ.	max.	
I <sub>RMS</sub>	RMS current	per terminal			70	A
T <sub>stg</sub>	storage temperature		-40		150	°C
T <sub>op</sub>	operation temperature		-40		150	°C
T <sub>vj</sub>	virtual junction temperature		-40		175	°C
Weight				6		g
M₀ Fc	mounting torque mounting force with clip		0.8 40		1.2 120	Nm N
d <sub>Spp/App</sub> d <sub>Spb/Apb</sub>	creepage distance on surface / striking distance through air	terminal to terminal terminal to backside	2.7 4.1			mm mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second t = 1 minute 50/60 Hz; RMS; $I_{ISOL} < 1 \text{ mA}$		3600 3000		V V



#### Part description

- D = Diode C = SiC
- G = Extreme fast
- 20 = Current Rating [A] C = Common Cathode
- 1200 = Reverse Voltage [V]
- HR = ISO247 (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	DCG20C1200HR	DCG20C1200HR	Tube	30	522960

Equival	ent Circuits for Simulation	*on die level, typical				
	⊢R₀	T <sub>vJ</sub> = 125°C	T <sub>vj</sub> = 175°C			
V <sub>0 max</sub>	threshold voltage	0.77	0.68	V		
$R_{0 max}$	slope resistance *	107	133	mΩ		

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### DCG20C1200HR

2x D3

1

D1

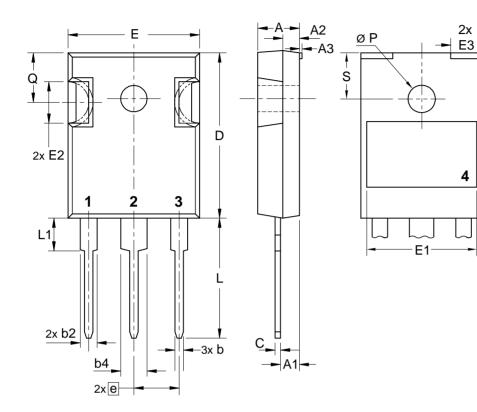
1

D2

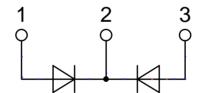
4

### tentative

#### Outlines ISO247



Dim.	Millimeter		Inches		
Dim.	min	max	min	max	
Α	4.70	5.30	0.185	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
A3	typ.	0.05	typ. 0.002		
b	0.99	1.40	0.039	0.055	
b2	1.65	2.39	0.065	0.094	
b4	2.59	3.43	0.102	0.135	
С	0.38	0.89	0.015	0.035	
D	20.79	21.45	0.819	0.844	
D1	typ.	8.90	typ.	yp. 0.350 yp. 0.114 yp. 0.039	
D2	typ.	2.90	typ.		
D3	typ.	1.00	typ.		
Е	15.49	16.24	0.610	0.639	
E1	typ.	13.45	typ.	0.530	
E2	4.31	5.48	0.170	70 0.216 yp. 0.157	
E3	typ.	4.00	typ.		
е	5.46	BSC	0.215 BSC		
L	19.80	20.30	0.780	0.799	
L1	-	4.49	-	0.177	
ØΡ	3.55	3.65	0.140	0.144	
Q	5.38	6.19	0.212	0.244	
S	6.14	BSC	0.242 BSC		



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## DCG20C1200HR

#### tentative

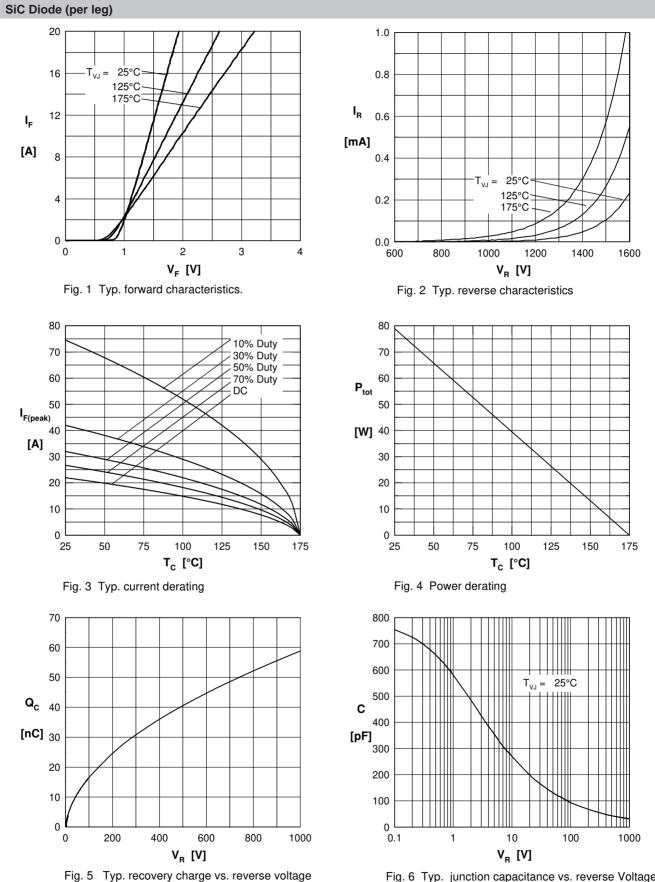


Fig. 6 Typ. junction capacitance vs. reverse Voltage

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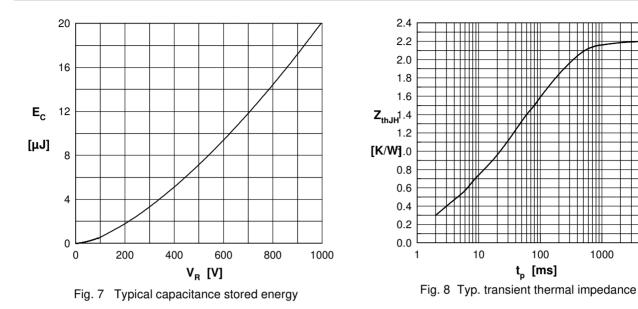
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DCG20C1200HR

tentative

10000

#### SiC Diode (per leg)



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